



Microelectronics

Lesson. 3 Carrier Transport in Semiconductor (Drift and Diffusion)

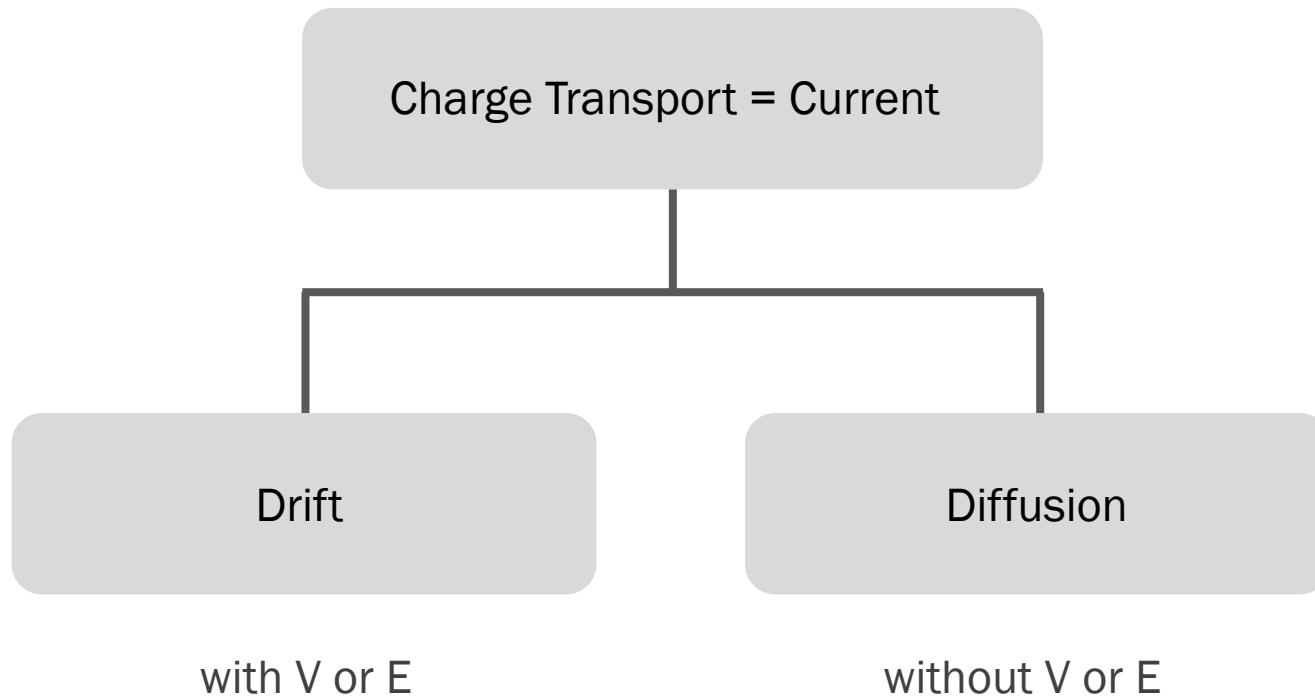
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Haena Kim

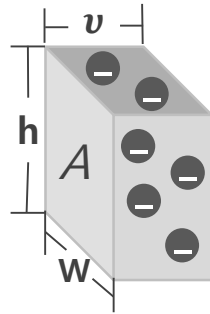
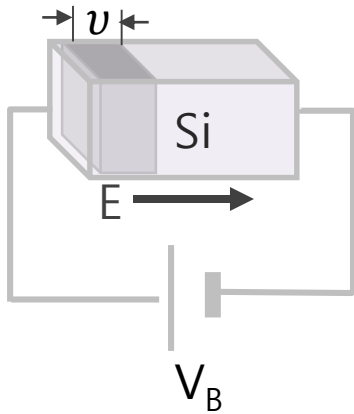


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Drift Current conduction due to electric field (just as Basic circuit)



$I =$ charges through A per sec.

$v =$ velocity of electrons

➔ $I =$ Total charge in volume ($w * h * v$)

∴ Total charge = $\frac{v \cdot w \cdot h \cdot n \cdot q}{\text{volume} \quad \text{quantity of charge}}$
of electrons

$$= |I|$$

$$= \mu_n \frac{V_B}{L} w h n q \rightarrow \frac{1}{R}$$

$$\therefore R = \frac{L}{\mu_n w h n q}$$

$$= \frac{1}{\mu_n n q} \cdot \frac{L}{A}$$

→ ρ

$$V = IR \quad v = \mu_n E$$

$$R = \rho \frac{L}{A} \quad E = \frac{V_B}{L}$$

Find I to calculate R

$$I = \mu_n \frac{V_B}{L} w h n q$$

$$J_n = \frac{I}{A}$$

$$J_n = \mu_n \frac{V_B}{L} n q$$

$$= \mu_n E n q \text{ [A/cm}^2\text{]}$$

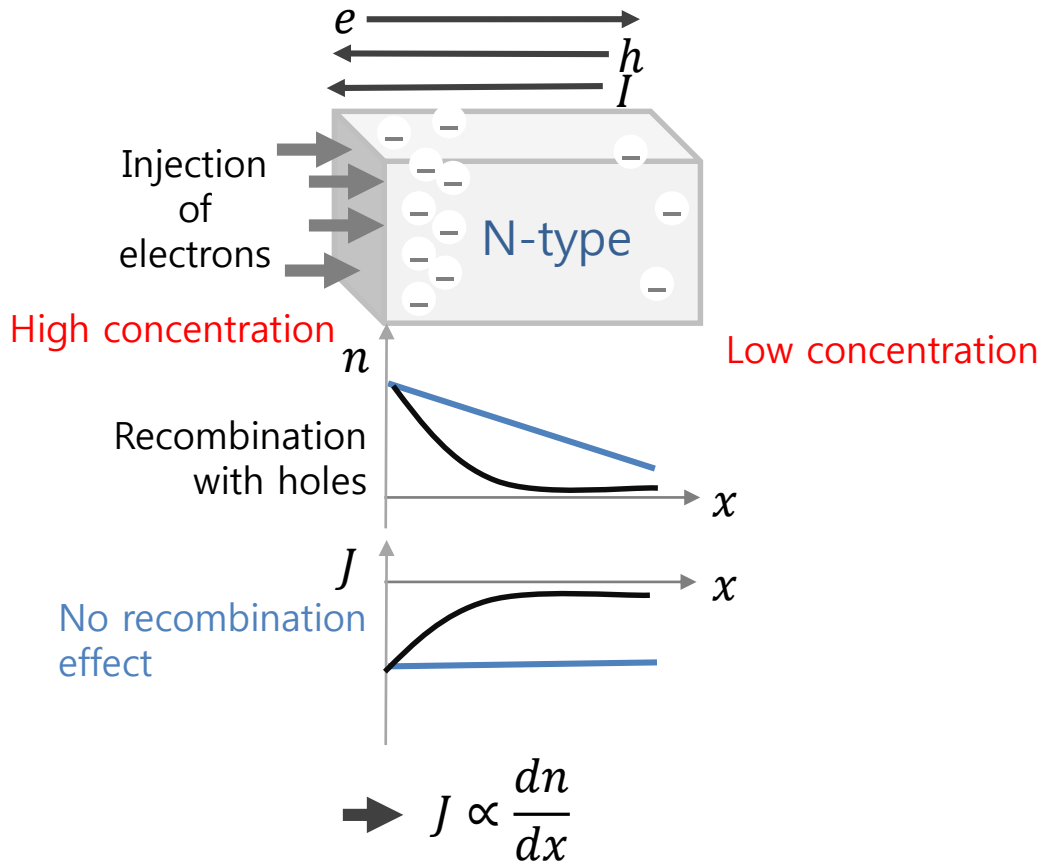
$$J_p = \mu_p E p q \text{ [A/cm}^2\text{]}$$

$$\mu_n = 1350 \text{ cm}^2/\text{V} \cdot \text{s}$$

$$\mu_p \approx 400 \text{ cm}^2/\text{V} \cdot \text{s}$$

$$\therefore \text{Total } J_{drift} = (\mu_n n + \mu_p p) E \cdot q$$

Diffusion Movement of charge carriers from a region of high concentration to a region of low concentration



$$J_n = Dn \frac{dn}{dx} q < 0$$

$$J_p = -Dp \frac{dp}{dx} q > 0 \quad (\because \frac{dp}{dx} < 0)$$

$$\therefore \text{Total } J_{diff} = \left(D_n \frac{dn}{dx} - D_p \frac{dp}{dx} \right) q$$

$$\frac{D}{\mu} = \frac{kT}{q}$$

Thermal voltage
26mV at $T = 300k$

Drift	Diffusion
Electric field	Difference of concentration
μ	D
$J_n = \mu_n E n q$	$J_n = D n \frac{dn}{dx} q$
$J_p = \mu_p E p q$	$J_p = -D p \frac{dp}{dx} q$
$J_{drift} = (\mu_n n + \mu_p p) E \cdot q$	$J_{diff} = \left(D_n \frac{dn}{dx} - D_p \frac{dp}{dx} \right) q$



경청해 주셔서 감사합니다.